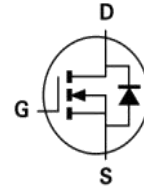


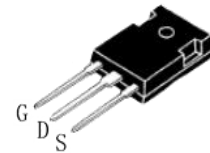
MAIN CHARACTERISTICS

I_D	3A
V_{DSS}	1500V
$R_{DS(on)-typ}$ (@ $V_{GS}=10V$)	5.4 Ω



FEATURES

- RoHS Compliant
- $R_{DS(ON),typ.}=5.4\ \Omega @V_{GS}=10V$
- Low Gate Charge Minimize Switching Loss
- Fast Recovery Body Diode



TO-247

APPLICATIONS

- Adaptor
- Charger
- SMPS Standby Power

MECHANICAL DATA

- Case: Molded plastic
- Mounting Position: Any
- Molded Plastic: UL Flammability Classification Rating 94V-0
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Solder bath temperature 275 $^{\circ}C$ maximum, 10s per JESD 22-B106

Product specification classification

Part Number	Package	Mode Name	Pack
CS3N150A6	TO-247	CS3N150A	Tube

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Symbol	Value	Unit
		247	
Drain-Source Voltage	V_{DS}	1500	V
Gate-Source Voltage	V_{GS}	± 30	V
Continue Drain Current	I_D	3	A
Pulsed Drain Current (Note1)	I_{DM}	12	A
Power Dissipation	P_D	90	W
Single Pulse Avalanche Energy (Note1)	E_{AS}	500	mJ
Operating Temperature Range	T_J	150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.38	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	50	°C/W

Note1:Pulse test: 300 μ s pulse width, 2 % duty cycle

Electrical Characteristics at Tc=25°C unless otherwise specified

Characteristics	Test Condition	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	BV_{DSS}	1500	-	-	V
Drain-Source Leakage Current	$V_{DS} = 1500\text{ V}, V_{GS} = 0\text{ V}$	I_{DSS}	-	-	1	μA
Gate Leakage Current	$V_{GS} = \pm 30\text{ V}, V_{DS} = 0\text{ V}$	I_{GSS}	-	-	± 100	nA
Gate-Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	$V_{GS(th)}$	2.5	-	4.5	V
Drain-Source On-State Resistance	$V_{GS} = 10\text{ V}, I_D = 2\text{ A}$	$R_{DS(on)}$	-	5.4	8.2	Ω
Forward Trans conductance	$V_{DS}=30\text{ V}, I_D = 3\text{ A}$	g_{fs}	-	3	-	S
Input Capacitance	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V},$ $f = 1\text{ MHz}$	C_{iss}	-	1600	-	pF
Output Capacitance		C_{oss}	-	100	-	pF
Reverse Transfer Capacitance		C_{rss}	-	33	-	pF
Turn-on Delay Time(Note2)	$I_D = 3\text{ A}, V_{DD} = 750\text{ V},$ $R_G = 4.7\text{ }\Omega, V_{GS} = 10\text{ V}$	$t_d(ON)$	-	25	-	ns
Rise Time(Note2)		t_r	-	48	-	ns
Turn-Off Delay Time(Note2)		$t_d(OFF)$	-	57	-	ns
Fall Time(Note2)		t_f	-	52	-	ns
Total Gate Charge(Note2)	$I_D = 3\text{ A}, V_{DD} = 750\text{ V},$ $V_{GS} = 10\text{ V}$	Q_G	-	36	-	nC
Gate to Source Charge(Note2)		Q_{GS}	-	9.5	-	nC
Gate to Drain Charge(Note2)		Q_{GD}	-	12	-	nC

Source-Drain Diode Characteristics at Ta=25°C unless otherwise specified

Characteristics	Test Condition	Symbo	Min.	Typ.	Max.	Unit
Maximun Body-Diode Continuous Current		I_S	-	-	3	A
Maximun Body-Diode Pulsed Current(Note2)		I_{SM}	-	-	12	A
Drain-Source Diode Forward Voltage	$I_{SD} = 3\text{ A}$	V_{SD}	-	-	1.5	V
Reverse Recovery Time(Note2)	$I_{SD} = 3\text{ A}, V_{GS} = 0\text{ V},$	t_{rr}	-	255	-	ns
Reverse Recovery Charge(Note2)	$dI_F / dt = 100\text{ A}/\mu\text{s}$	Q_{rr}	-	1.1	-	μC

Note2:Pulse test: 300 μ s pulse width, 2 % duty cycle

RATINGS AND CHARACTERISTIC CURVES

Figure 1. Maximum Transient Thermal Impedance

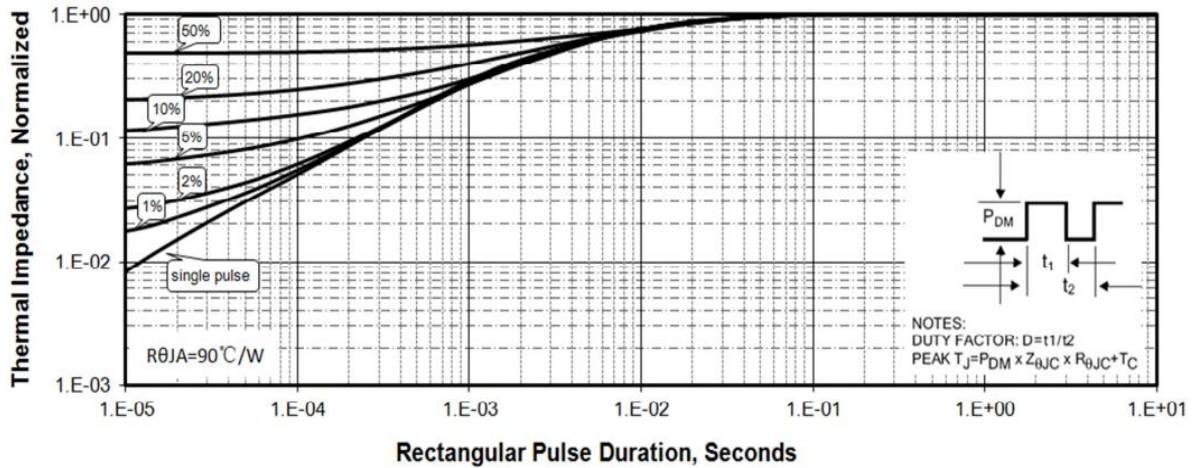


Figure 2 . Max. Power Dissipation vs Case Temperature

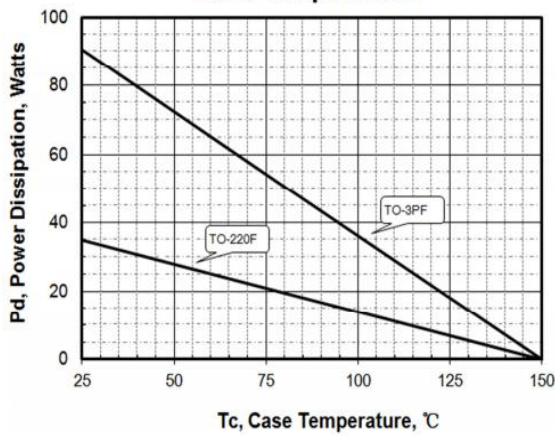


Figure 3 .Maximum Continuous Drain Current vs Tc

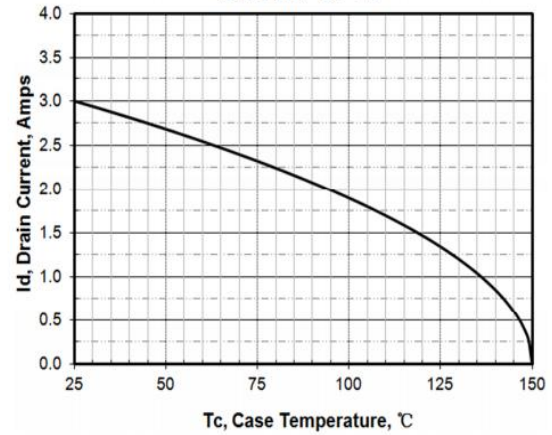


Figure 4. Output Characteristics

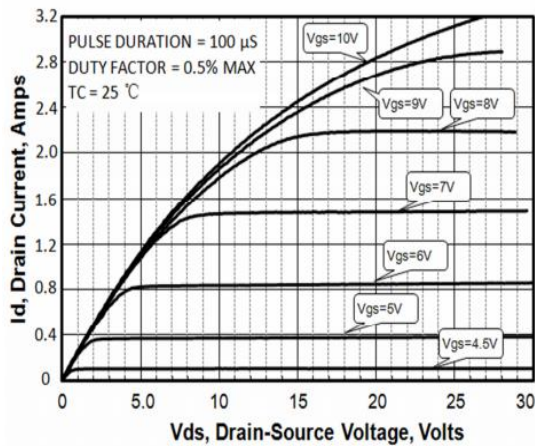
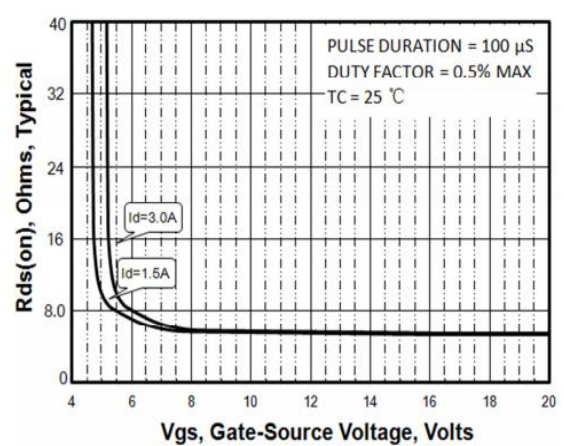


Figure 5. Rdson vs Gate Voltage



RATINGS AND CHARACTERISTIC CURVES

Figure 6. Peak Current Capability

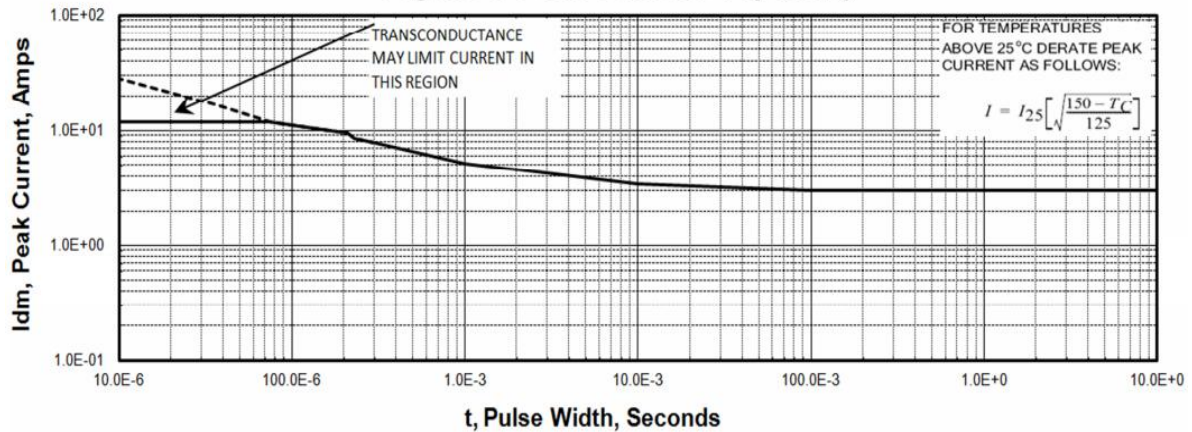


Figure 7. Transfer Characteristics

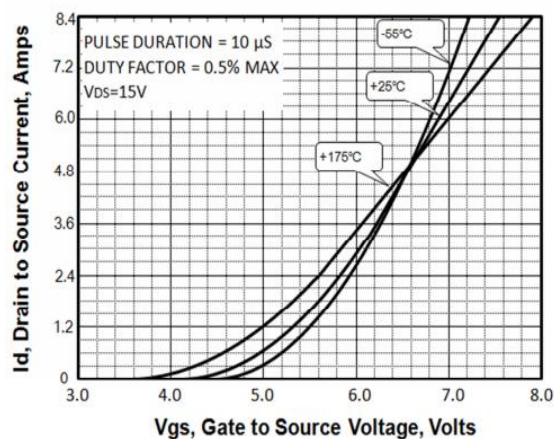


Figure 8. Unclamped Inductive Switching Capability

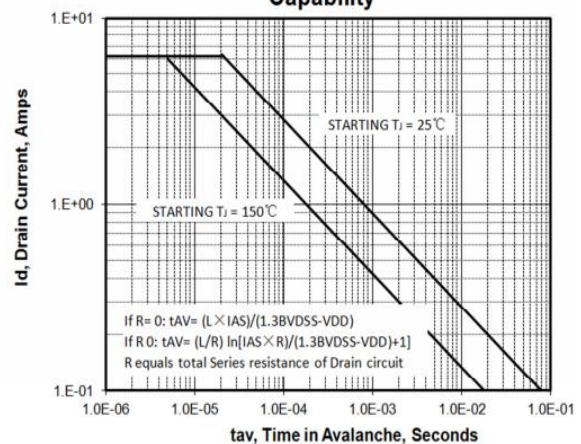


Figure 9. Drain to Source ON Resistance vs Drain Current

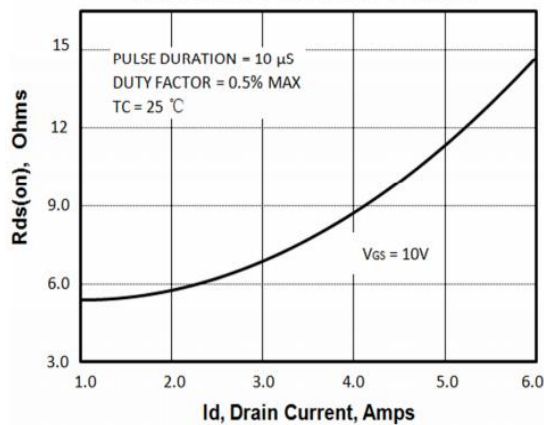


Figure 10. Rds(on) vs Junction Temperature

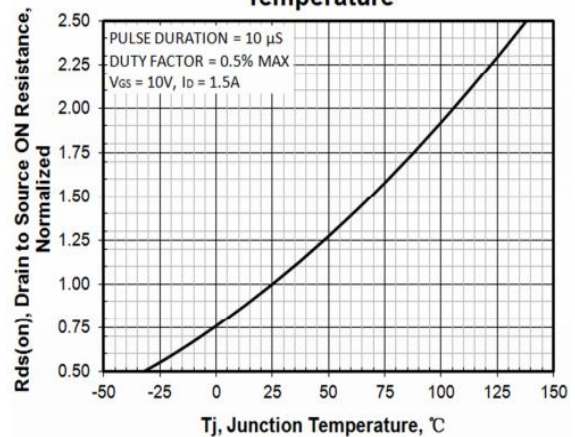


Figure 11. Breakdown Voltage vs Temperature

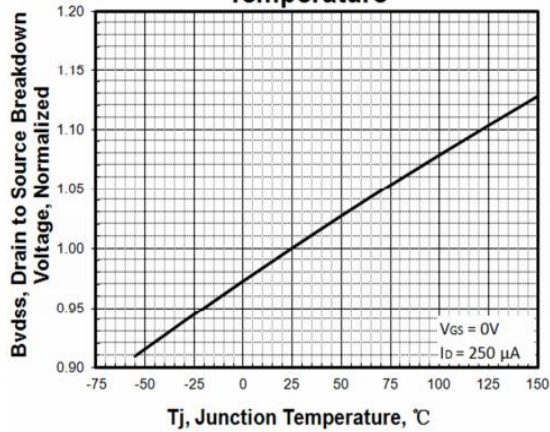


Figure 12. Threshold Voltage vs Temperature

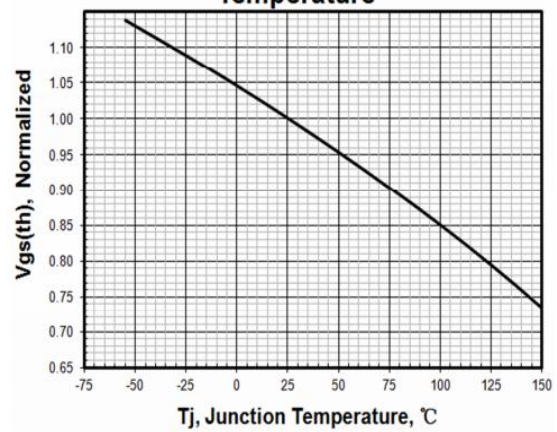


Figure 13 . Maximum Safe Operating Area(TO-3PF)

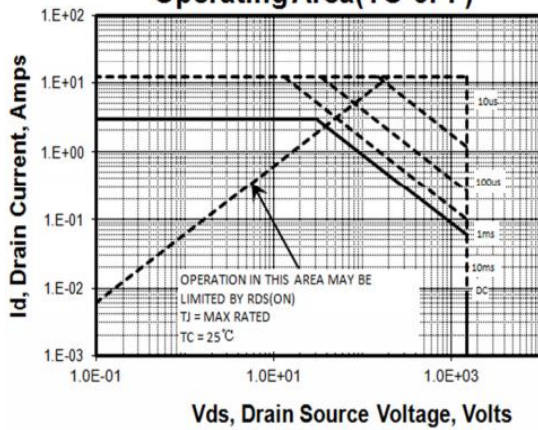


Figure 14 . Maximum Safe Operating Area(TO-220F)

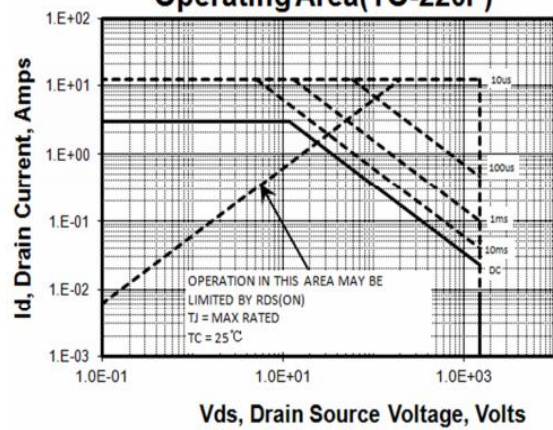


Figure 15. Capacitance vs Vds

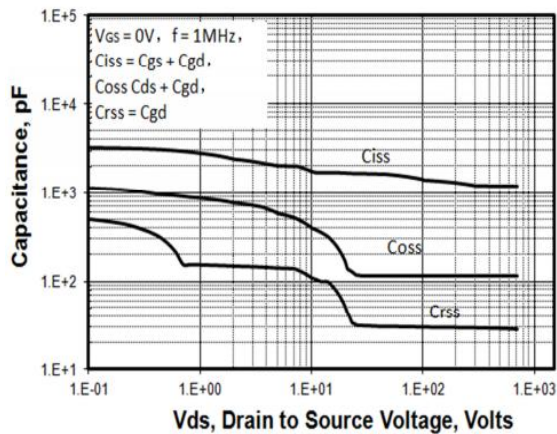
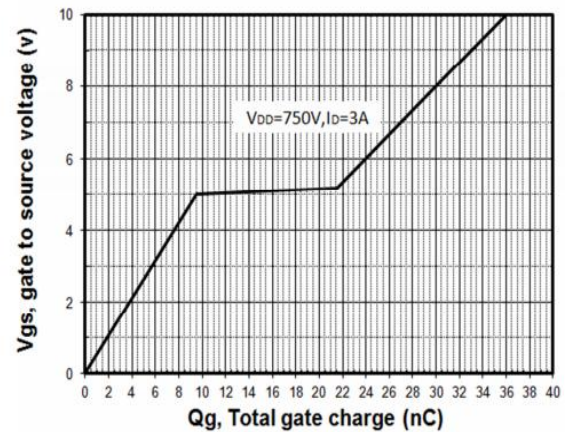


Figure 16 . Typical Gate Charge

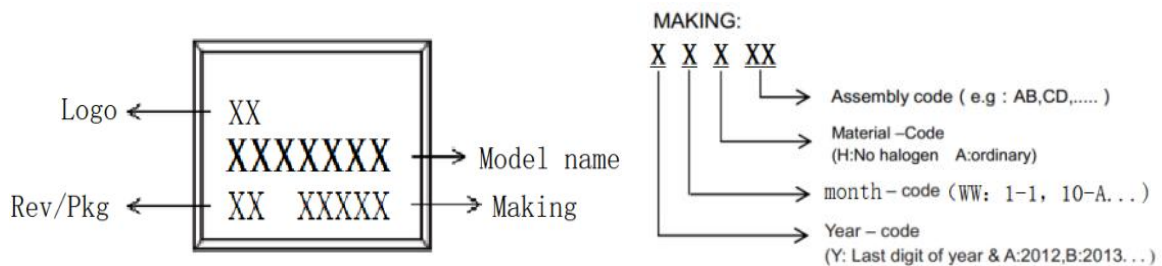


Marking on the body

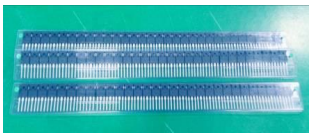
TO-247

Dim.	Min.	Max.
A	15	16
B	20	21
C	41	42
D	5	6
E	4	5
F	2.5	3.5
G	1.75	2.5
H	3	3.5
I	8	10
J	4.9	5.1
K	1.9	2.1
L	3.5	4
M	4.75	5.25
N	2	3
O	0.55	0.75
P	Typ 5.08	
Q	1.2	1.3

Marking on the body



packing instruction

PKG	最小包装	内盒	外箱
TO-247			
	30PCS/管	600pcs/盒	3000pcs/箱

Notice

All product,product specifications and data are subject to change without notice to improve.The right to explain is owned by LINGXUN electronics company.

Confirm that operation temperature is within the specified range described in the product specification. Avoid applying poer exceeding normal ratedpoer; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.

LINGXUN electronics shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this documentpoer; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.